MOSFETs Silicon N-Channel MOS

# SSM3K336R

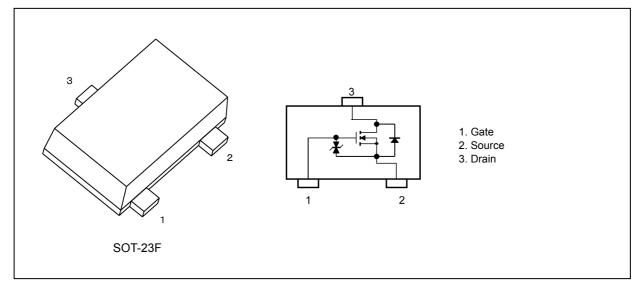
### 1. Applications

- Power Management Switches
- DC-DC Converters

## 2. Features

- (1) 4.5 V gate drive voltage.

## 3. Packaging and Internal Circuit



## 4. Absolute Maximum Ratings (Note) (Unless otherwise specified, $T_a = 25^{\circ}C$ )

	Characteristics		Symbol	Rating	Unit
Drain-source voltage			V <sub>DSS</sub>	30	V
Gate-source voltage			V <sub>GSS</sub>	±20	
Drain current (DC)		(Note 1)	Ι <sub>D</sub>	3	A
Drain current (pulsed)		(Note 1,2)	I <sub>DP</sub>	8	
Power dissipation		(Note 3)	PD	1	W
Power dissipation	(t ≤ 10 s)	(Note 3)	PD	2	W
Channel temperature			T <sub>ch</sub>	150	°C
Storage temperature			T <sub>stg</sub>	-55 to 150	

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

- Note 1: Ensure that the channel temperature does not exceed 150°C.
- Note 2: Pulse width (PW)  $\leq$  10 ms, duty  $\leq$  1%
- Note 3: Device mounted on a FR4 board.(25.4 mm  $\times$  25.4 mm  $\times$  1.6 mm, Cu Pad: 645 mm<sup>2</sup>)
- Note: The MOSFETs in this device are sensitive to electrostatic discharge. When handling this device, the worktables, operators, soldering irons and other objects should be protected against anti-static discharge.
- Note: The channel-to-ambient thermal resistance, R<sub>th(ch-a)</sub>, and the power dissipation, P<sub>D</sub>, vary according to the board material, board area, board thickness and pad area. When using this device, be sure to take heat dissipation fully into account.

#### 5. Electrical Characteristics

## 5.1. Static Characteristics (Unless otherwise specified, $T_a = 25^{\circ}C$ )

Characteristics		Symbol	Test Condition	Min	Тур.	Max	Unit
Gate leakage current		I <sub>GSS</sub>	$V_{GS}$ = ±20 V, $V_{DS}$ = 0 V	_	_	±10	μA
Drain cut-off current		I <sub>DSS</sub>	$V_{DS}$ = 30 V, $V_{GS}$ = 0 V			1	
Drain-source breakdown voltage		V <sub>(BR)DSS</sub>	I <sub>D</sub> = 10 mA, V <sub>GS</sub> = 0 V	30	—	—	V
Drain-source breakdown voltage	(Note 1)	V <sub>(BR)DSX</sub>	$I_{\rm D}$ = 10 mA, $V_{\rm GS}$ = -20 V	15	_	_	
Gate threshold voltage	(Note 2)	V <sub>th</sub>	V <sub>DS</sub> = 10 V, I <sub>D</sub> = 0.1 mA	1.3	_	2.5	
Drain-source on-resistance	(Note 3)	R <sub>DS(ON)</sub>	$I_D$ = 2.0 A, $V_{GS}$ = 10 V	—	67	95	mΩ
			$I_D$ = 1.0 A, $V_{GS}$ = 4.5 V		100	140	
Forward transfer admittance	(Note 3)	Y <sub>fs</sub>	V <sub>DS</sub> = 10 V, I <sub>D</sub> = 1.0 A	2.5	5	_	S

Note 1: If a reverse bias is applied between gate and source, this device enters V<sub>(BR)DSX</sub> mode. Note that the drainsource breakdown voltage is lowered in this mode.

Note 2: Let  $V_{th}$  be the voltage applied between gate and source that causes the drain current (I<sub>D</sub>) to below (0.1 mA for this device). Then, for normal switching operation,  $V_{GS(ON)}$  must be higher than  $V_{th}$ , and  $V_{GS(OFF)}$  must be lower than  $V_{th}$ . This relationship can be expressed as:  $V_{GS(OFF)} < V_{th} < V_{GS(ON)}$ . Take this into consideration when using the device.

Note 3: Pulse measurement.

#### 5.2. Dynamic Characteristics (Unless otherwise specified, $T_a = 25^{\circ}C$ )

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Input capacitance	C <sub>iss</sub>	V <sub>DS</sub> = 15 V, V <sub>GS</sub> = 0 V,	_	126	—	pF
Reverse transfer capacitance	C <sub>rss</sub>	f = 1 MHz	_	8	—	
Output capacitance	C <sub>oss</sub>		_	26	_	
Switching time (turn-on time)		V <sub>DD</sub> = 15 V, I <sub>D</sub> = 0.5 A V <sub>GS</sub> = 0 to 4.5 V, R <sub>G</sub> = 10 Ω,	_	7	—	ns
Switching time (turn-off time)	t <sub>off</sub>	Duty $\leq$ 1%, Input: t <sub>r</sub> , t <sub>f</sub> < 5 ns Common source, See Chapter 5.3	_	8	_	

## 5.3. Switching Time Test Circuit

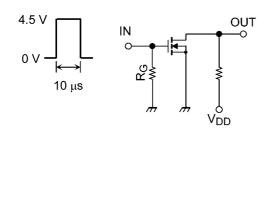


Fig. 5.3.1 Test Circuit of Switching Time

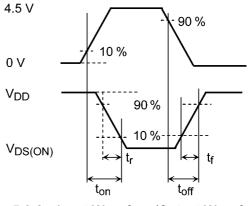


Fig. 5.3.2 Input Waveform/Output Waveform

## 5.4. Gate Charge Characteristics (Unless otherwise specified, $T_a = 25^{\circ}C$ )

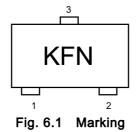
Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Total gate charge (gate-source plus gate-drain)	Qg	V <sub>DD</sub> = 15 V, V <sub>GS</sub> = 4.5V,	_	1.7	—	nC
Gate-source charge 1	Q <sub>gs1</sub>	I <sub>D</sub> = 3.0 A	_	0.8	—	
Gate-drain charge	Q <sub>gd</sub>		_	0.7		

## 5.5. Source-Drain Characteristics (Unless otherwise specified, $T_a = 25^{\circ}C$ )

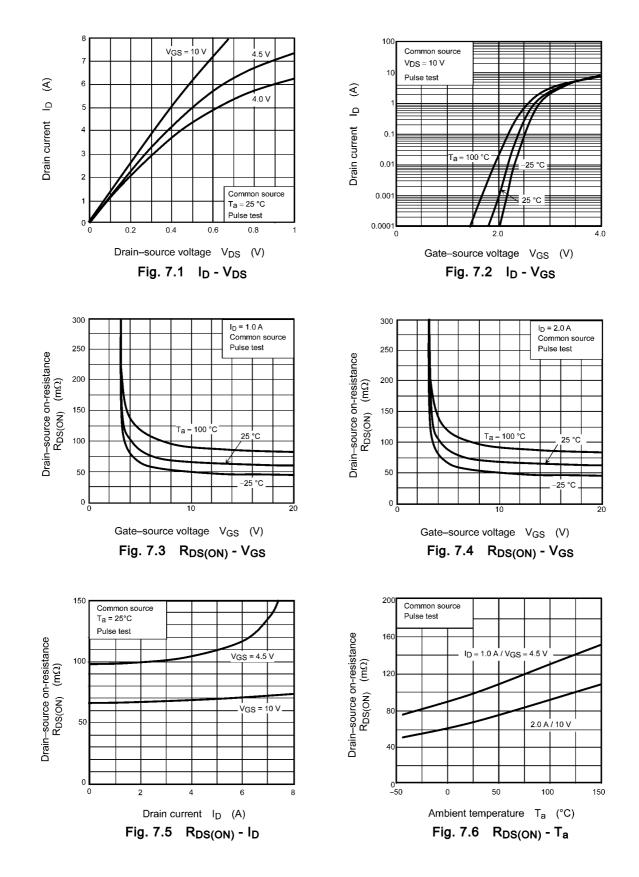
Characteristics		Symbol	Test Condition	Min	Тур.	Max	Unit
Diode forward voltage	(Note 1)	V <sub>DSF</sub>	$I_{\rm D}$ = -3.0 A, $V_{\rm GS}$ = 0 V		-0.89	-1.2	V

Note 1: Pulse measurement.

#### 6. Marking



## 7. Characteristics Curves (Note)



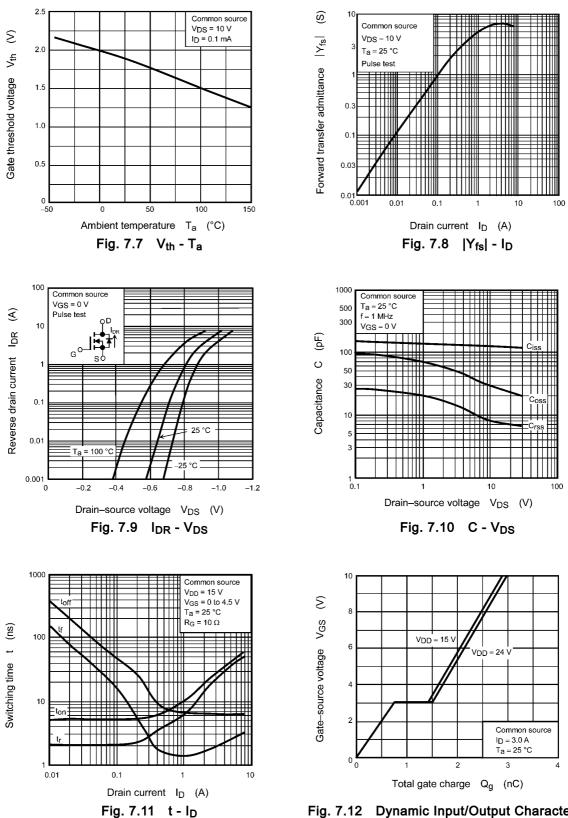
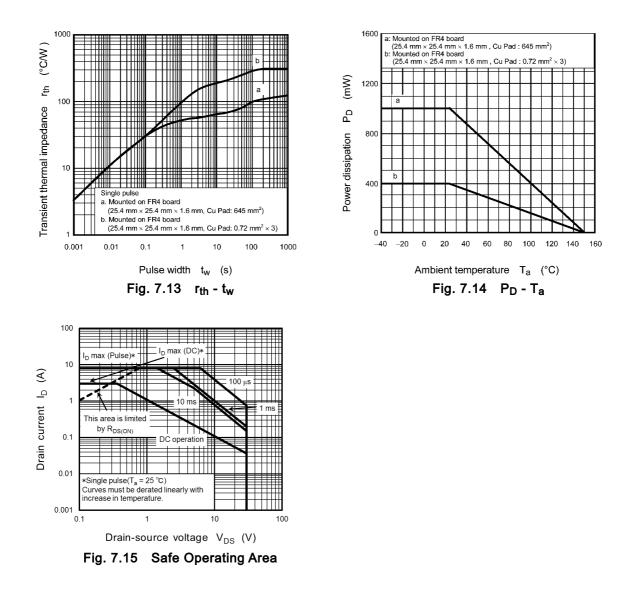


Fig. 7.12 Dynamic Input/Output Characteristics



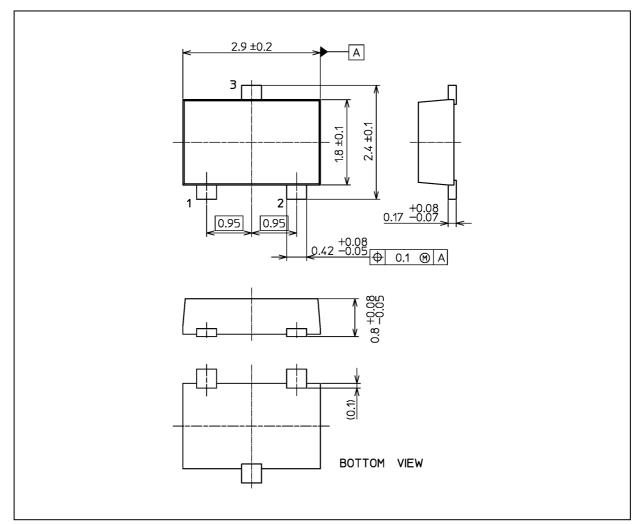
Note: The above characteristics curves are presented for reference only and not guaranteed by production test, unless otherwise noted.



## SSM3K336R

## Package Dimensions

Unit: mm



Weight: 0.011 g (typ.)

Package Name(s)					
TOSHIBA: 2-3Z1S					
Nickname: SOT-23F					

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